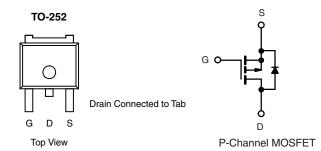


Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.010			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.024			
I _D (A)	- 50			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- \bullet 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn



ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD45P03-12-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 20	¬	
Continuous Drain Current	T _C = 25 °C ^a	1	- 50		
	T _C = 125 °C	l _D	- 37		
Continuous Source Current (Diode Conduction) ^a		I _S	- 50	А	
Pulsed Drain Current ^b		I _{DM}	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 31		
Single Pulse Avalanche Energy	L = U. I IIIII	E _{AS}	48	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	71	W	
	T _C = 125 °C	P_{D}	23	VV	
Operating Junction and Storage Temperatur	re Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	2.1	C/ VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1				·	ı		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 30	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		- 2.0	- 2.5	\ \	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = - 30 V	-	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	μA	
-		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V _{GS} = - 10 V	I _D = - 15 A	-	0.008	0.010	Ω	
Dunin Course On Chata Basistanas		V _{GS} = - 10 V	I _D = - 15 A, T _J = 125 °C	-	-	0.015		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 15 A, T _J = 175 °C	-	-	0.017		
		V _{GS} = - 4.5 V	I _D = - 12 A	-	0.019	0.024		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		-	34	-	S	
Dynamic ^b		<u> </u>						
Input Capacitance	C _{iss}			-	2794	3495		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 15 V, f = 1 MHz	-	616	770	pF	
Reverse Transfer Capacitance	C _{rss}			-	470	590		
Total Gate Charge ^c	Qg			-	55.3	83		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -45 \text{ A}$	-	7.3	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	14	-		
Gate Resistance	R_g	f = 1 MHz		1.40	2.86	4.50	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	11	16.5		
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 0.33 Ω $I_D \cong$ - 45 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	11	16.5	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	29	43.5		
Fall Time ^c	t _f			-	19	28.5		
Source-Drain Diode Ratings and Chara	acteristics ^b	•						
Pulsed Current ^a	I _{SM}			-	-	- 200	Α	
Forward Voltage	V _{SD}	$I_F = -40 \text{ A}, V_{GS} = 0$		-	- 0.9	- 1.5	V	

Notes

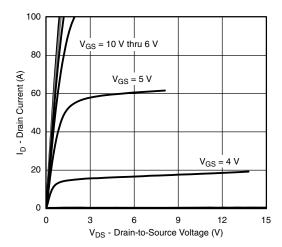
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

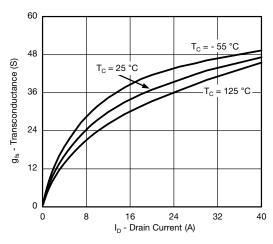


Automotive P-Channel 30 V (D-S) 175 °C MOSFET

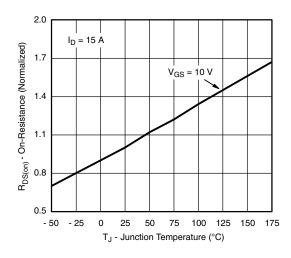
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



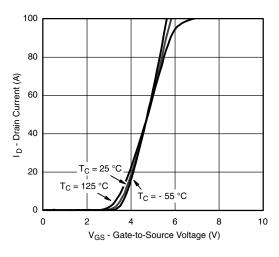
Output Characteristics



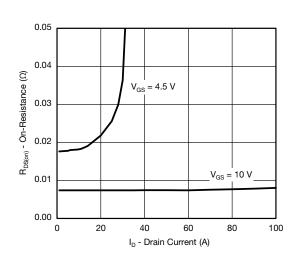
Transconductance



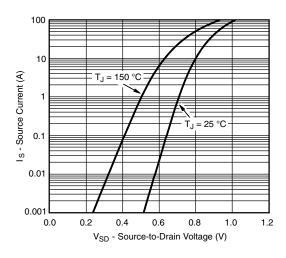
On-Resistance vs. Junction Temperature



Transfer Characteristics



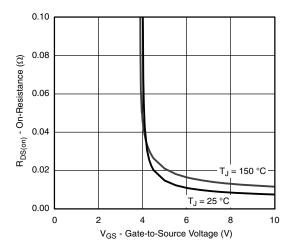
On-Resistance vs. Drain Current



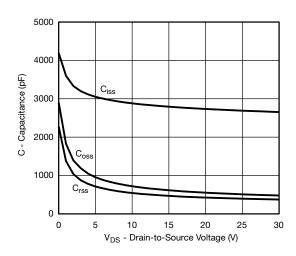
Source Drain Diode Forward Voltage

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

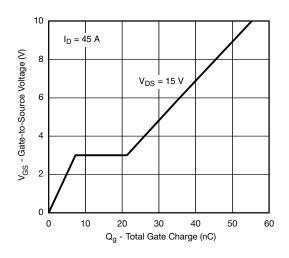
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



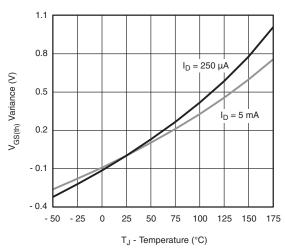
On-Resistance vs. Gate-to-Source Voltage



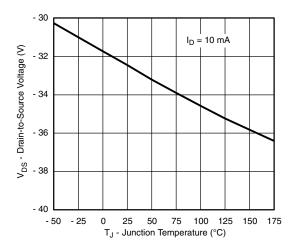
Capacitance



Gate Charge



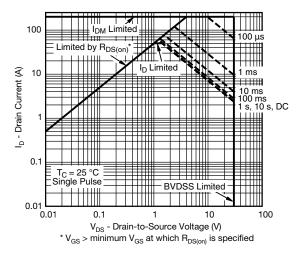
Threshold Voltage



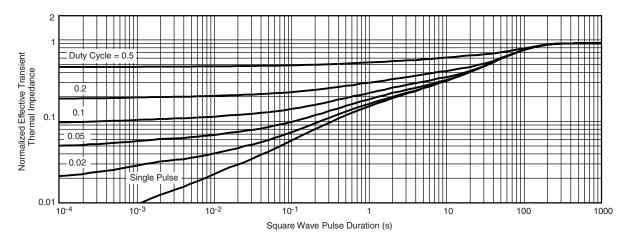
Drain Source Breakdown vs. Junction Temperature

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



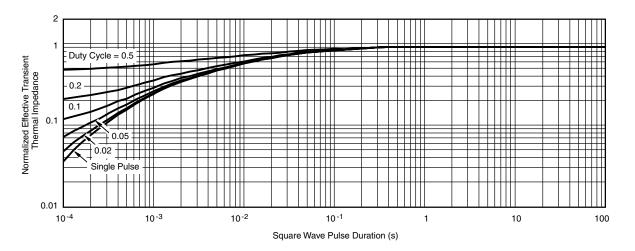
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



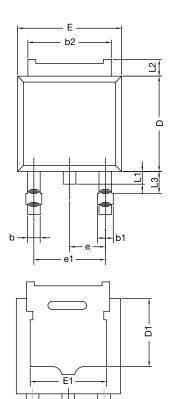
Normalized Thermal Transient Impedance, Junction-to-Case

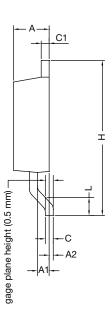
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





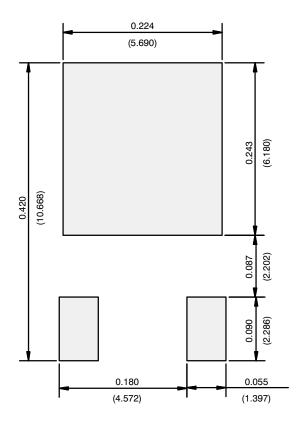
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Automotive P-Channel 30 V (D-S) 175 °C MOSFET

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

freestyle Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on it s or their behalf (collectively, "freestyle"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

freestyle makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vi shay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain type s of applications are based on freestyle's knowledge of typical requirements that are often placed on freestyle products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specification s may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify freestyle's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, freestyle products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the freestyle product could result in personal injury or death. Customers using or selling freestyle products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold freestyle and its distributors harmless from and against an y and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vis hay

Material Category Policy

freestyle Intertechnology, Inc. hereby certi fies that all its products that are id entified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some freestyle documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002 /95/EC conform to Directive 2011/65/EU.